

# Thyristor Modules

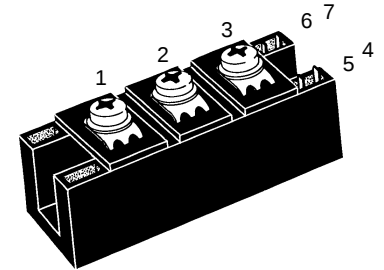
## Thyristor/Diode Modules

$$I_{TRMS} = 2 \times 300 \text{ A}$$

$$I_{TAVM} = 2 \times 130 \text{ A}$$

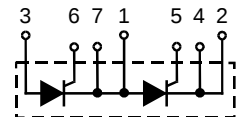
$$V_{RRM} = 800-1800 \text{ V}$$

| $V_{RSM}$<br>$V_{DSM}$<br>V | $V_{RRM}$<br>$V_{DRM}$<br>V | Type          |               |
|-----------------------------|-----------------------------|---------------|---------------|
|                             |                             | Version 1     | Version 1     |
| 900                         | 800                         | MCC 132-08io1 | MCD 132-08io1 |
| 1300                        | 1200                        | MCC 132-12io1 | MCD 132-12io1 |
| 1500                        | 1400                        | MCC 132-14io1 | MCD 132-14io1 |
| 1700                        | 1600                        | MCC 132-16io1 | MCD 132-16io1 |
| 1900                        | 1800                        | MCC 132-18io1 | MCD 132-18io1 |

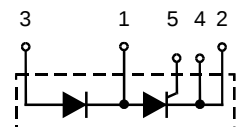


| Symbol                                       | Test Conditions                                                                                                                                           |                                                                            | Maximum Ratings                  |                                                  |
|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------|----------------------------------|--------------------------------------------------|
| $I_{TRMS}, I_{FRMS}$<br>$I_{TAVM}, I_{FAVM}$ | $T_{VJ} = T_{VJM}$<br>$T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$                                                                                    |                                                                            | 300<br>130                       | A<br>A                                           |
| $I_{TSM}, I_{FSM}$                           | $T_{VJ} = 45^\circ\text{C};$<br>$V_R = 0$                                                                                                                 | $t = 10 \text{ ms (50 Hz), sine}$<br>$t = 8.3 \text{ ms (60 Hz), sine}$    | 4750<br>5080                     | A<br>A                                           |
|                                              | $T_{VJ} = T_{VJM}$<br>$V_R = 0$                                                                                                                           | $t = 10 \text{ ms (50 Hz), sine}$<br>$t = 8.3 \text{ ms (60 Hz), sine}$    | 4230<br>4530                     | A<br>A                                           |
| $\int i^2 dt$                                | $T_{VJ} = 45^\circ\text{C}$<br>$V_R = 0$                                                                                                                  | $t = 10 \text{ ms (50 Hz), sine}$<br>$t = 8.3 \text{ ms (60 Hz), sine}$    | 113 000<br>108 000               | $\text{A}^2\text{s}$<br>$\text{A}^2\text{s}$     |
|                                              | $T_{VJ} = T_{VJM}$<br>$V_R = 0$                                                                                                                           | $t = 10 \text{ ms (50 Hz), sine}$<br>$t = 8.3 \text{ ms (60 Hz), sine}$    | 89 500<br>86 200                 | $\text{A}^2\text{s}$<br>$\text{A}^2\text{s}$     |
| $(di/dt)_{cr}$                               | $T_{VJ} = T_{VJM}$<br>$f = 50 \text{ Hz}, t_p = 200 \mu\text{s}$<br>$V_D = 2/3 V_{DRM}$<br>$I_G = 0.5 \text{ A}$<br>$di_G/dt = 0.5 \text{ A}/\mu\text{s}$ | repetitive, $I_T = 500 \text{ A}$<br>non repetitive, $I_T = 500 \text{ A}$ | 150<br>500                       | $\text{A}/\mu\text{s}$<br>$\text{A}/\mu\text{s}$ |
| $(dv/dt)_{cr}$                               | $T_{VJ} = T_{VJM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)                                                                                  | $V_{DR} = 2/3 V_{DRM}$                                                     | 1000                             | $\text{V}/\mu\text{s}$                           |
| $P_{GM}$                                     | $T_{VJ} = T_{VJM}$<br>$I_T = I_{TAVM}$                                                                                                                    | $t_p = 30 \mu\text{s}$<br>$t_p = 500 \mu\text{s}$                          | 120<br>60<br>8                   | W<br>W<br>W                                      |
| $P_{GAV}$                                    |                                                                                                                                                           |                                                                            | 8                                | W                                                |
| $V_{RGM}$                                    |                                                                                                                                                           |                                                                            | 10                               | V                                                |
| $T_{VJ}$                                     |                                                                                                                                                           |                                                                            | -40...+125                       | $^\circ\text{C}$                                 |
| $T_{VJM}$                                    |                                                                                                                                                           |                                                                            | 125                              | $^\circ\text{C}$                                 |
| $T_{stg}$                                    |                                                                                                                                                           |                                                                            | -40...+125                       | $^\circ\text{C}$                                 |
| $V_{ISOL}$                                   | 50/60 Hz, RMS<br>$I_{ISOL} \leq 1 \text{ mA}$                                                                                                             | $t = 1 \text{ min}$<br>$t = 1 \text{ s}$                                   | 3000<br>3600                     | V~<br>V~                                         |
| $M_d$                                        | Mounting torque (M6)<br>Terminal connection torque (M6)                                                                                                   |                                                                            | 2.25-2.75/20-25<br>4.5-5.5/40-48 | Nm/lb.in.<br>Nm/lb.in.                           |
| Weight                                       | Typical including screws                                                                                                                                  |                                                                            | 125                              | g                                                |

MCC



MCD



### Features

- International standard package
- Direct copper bonded  $\text{Al}_2\text{O}_3$  -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Keyed gate/cathode twin pins

### Applications

- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

### Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.  
IXYS reserves the right to change limits, test conditions and dimensions

| Symbol             | Test Conditions                                                                                                                                                                      | Characteristic Values |
|--------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|
| $I_{RRM}, I_{DRM}$ | $T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$                                                                                                                                     | 10 mA                 |
| $V_T, V_F$         | $I_T, I_F = 300 \text{ A}; T_{VJ} = 25^\circ\text{C}$                                                                                                                                | 1.36 V                |
| $V_{T0}$           | For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )                                                                                                                    | 0.8 V                 |
| $r_T$              |                                                                                                                                                                                      | 1.5 mΩ                |
| $V_{GT}$           | $V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$                                                                                                                                       | 2.5 V                 |
|                    | $T_{VJ} = -40^\circ\text{C}$                                                                                                                                                         | 2.6 V                 |
| $I_{GT}$           | $V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$                                                                                                                                       | 150 mA                |
|                    | $T_{VJ} = -40^\circ\text{C}$                                                                                                                                                         | 200 mA                |
| $V_{GD}$           | $T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$                                                                                                                                                | 0.2 V                 |
| $I_{GD}$           |                                                                                                                                                                                      | 10 mA                 |
| $I_L$              | $T_{VJ} = 25^\circ\text{C}; t_p = 30 \mu\text{s}; V_D = 6 \text{ V}$<br>$I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$                                                   | 300 mA                |
| $I_H$              | $T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$                                                                                                                      | 200 mA                |
| $t_{gd}$           | $T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$<br>$I_G = 0.5 \text{ A}; di_G/dt = 0.5 \text{ A}/\mu\text{s}$                                                                         | 2 μs                  |
| $t_q$              | $T_{VJ} = T_{VJM}; I_T = 160 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ typ.<br>$V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$ | 150 μs                |
| $Q_S$              | $T_{VJ} = T_{VJM}; I_T, I_F = 300 \text{ A}, -di/dt = 50 \text{ A}/\mu\text{s}$                                                                                                      | 550 μC                |
| $I_{RM}$           |                                                                                                                                                                                      | 235 A                 |
| $R_{thJC}$         | per thyristor/diode; DC current per module                                                                                                                                           | 0.23 K/W              |
| $R_{thJK}$         | per thyristor/diode; DC current per module                                                                                                                                           | 0.115 K/W             |
|                    | other values see Fig. 8/9                                                                                                                                                            | 0.33 K/W              |
|                    |                                                                                                                                                                                      | 0.165 K/W             |
| $d_s$              | Creepage distance on surface                                                                                                                                                         | 12.7 mm               |
| $d_A$              | Strike distance through air                                                                                                                                                          | 9.6 mm                |
| $a$                | Maximum allowable acceleration                                                                                                                                                       | 50 m/s <sup>2</sup>   |

Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) } UL 758, style 1385,  
Type ZY 180R (R = right for pin pair 6/7) } CSA class 5851, guide 460-1-1

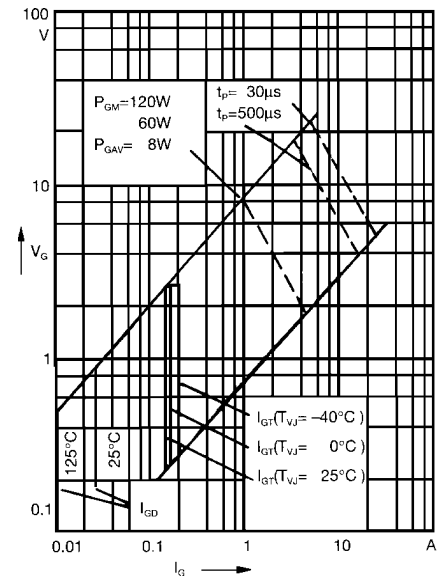


Fig. 1 Gate trigger characteristics

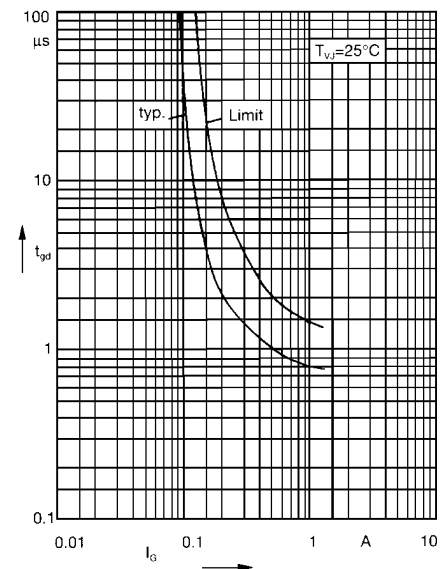
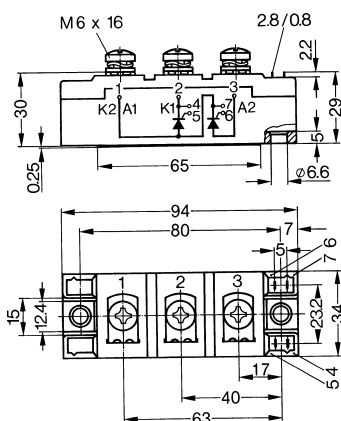


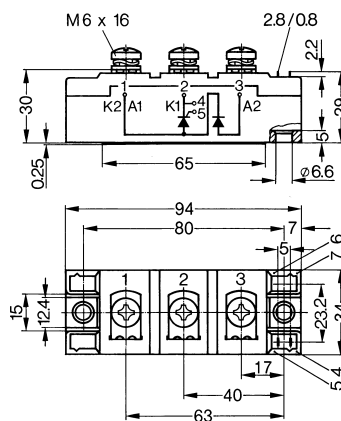
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

MCC



MCD



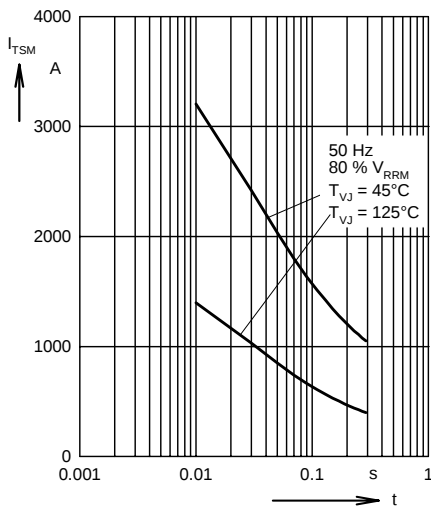


Fig. 3 Surge overload current  
 $I_{TSM}$ ,  $I_{FSM}$ : Crest value,  $t$ : duration

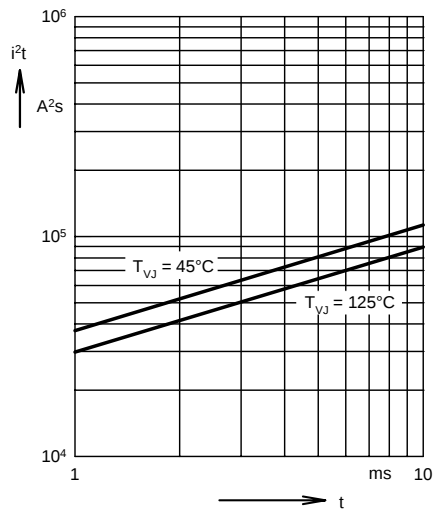


Fig. 4  $i^2t$  versus time (1-10 ms)

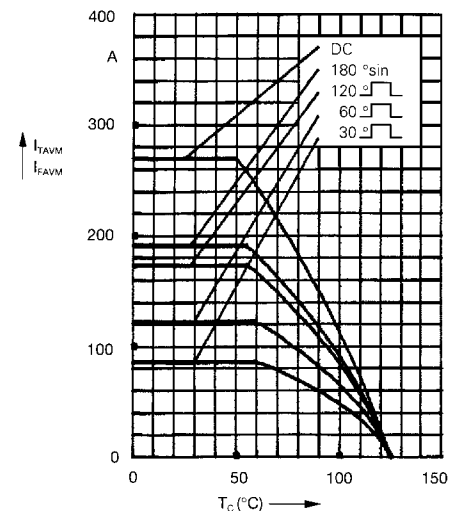


Fig. 4a Maximum forward current at case temperature

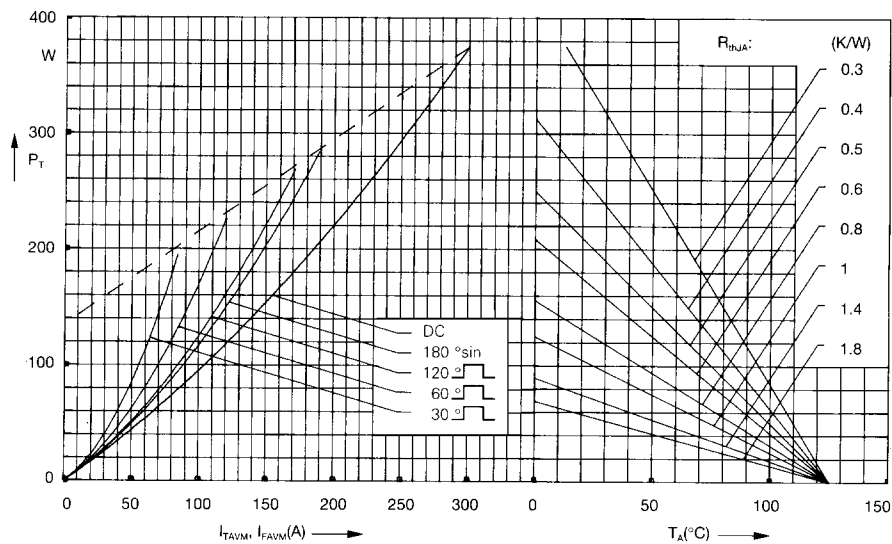


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

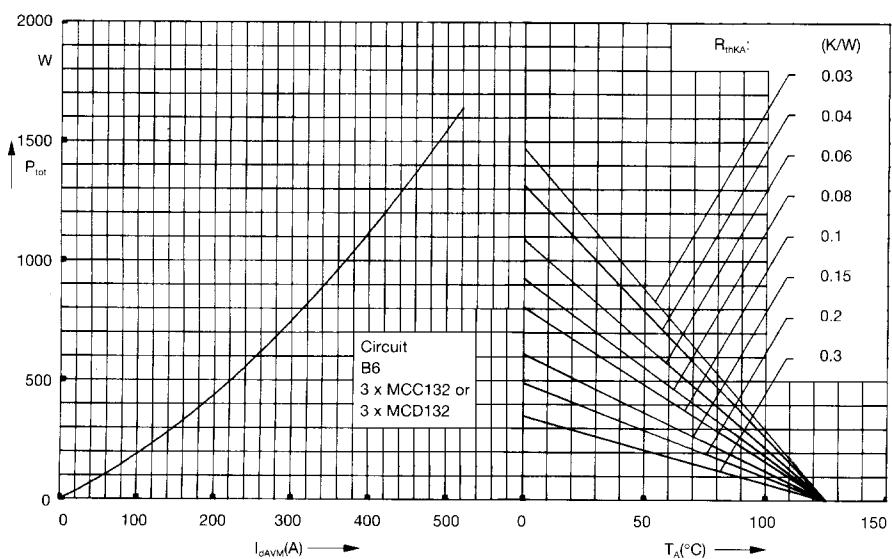


Fig. 6 Three phase rectifier bridge:  
Power dissipation versus direct output current and ambient temperature

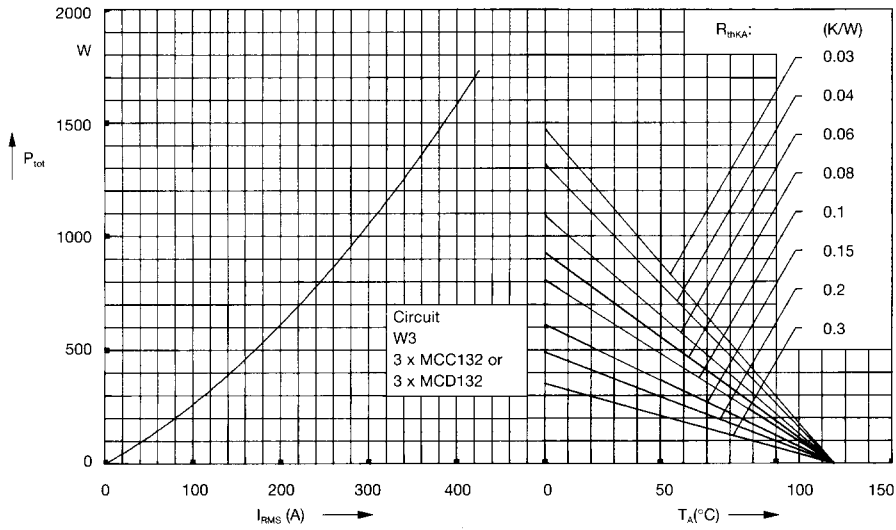


Fig. 7 Three phase AC-controller:  
Power dissipation versus RMS  
output current and ambient  
temperature

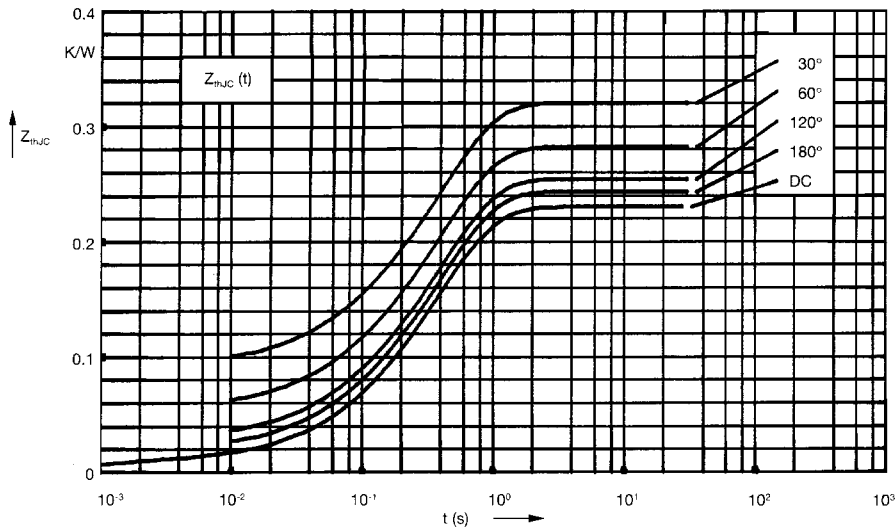


Fig. 8 Transient thermal impedance  
junction to case (per thyristor or  
diode)

$R_{thJC}$  for various conduction angles d:

| d    | $R_{thJC}$ (K/W) |
|------|------------------|
| DC   | 0.230            |
| 180° | 0.244            |
| 120° | 0.255            |
| 60°  | 0.283            |
| 30°  | 0.321            |

Constants for  $Z_{thJC}$  calculation:

| i | $R_{thi}$ (K/W) | $t_i$ (s) |
|---|-----------------|-----------|
| 1 | 0.0095          | 0.001     |
| 2 | 0.0175          | 0.065     |
| 3 | 0.203           | 0.4       |

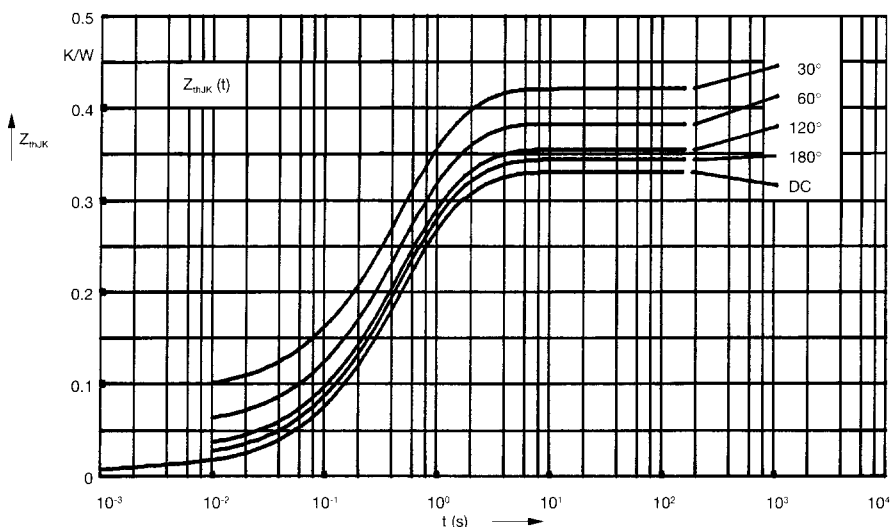


Fig. 9 Transient thermal impedance  
junction to heatsink (per thyristor  
or diode)

$R_{thJK}$  for various conduction angles d:

| d    | $R_{thJK}$ (K/W) |
|------|------------------|
| DC   | 0.330            |
| 180° | 0.344            |
| 120° | 0.355            |
| 60°  | 0.383            |
| 30°  | 0.421            |

Constants for  $Z_{thJK}$  calculation:

| i | $R_{thi}$ (K/W) | $t_i$ (s) |
|---|-----------------|-----------|
| 1 | 0.0095          | 0.001     |
| 2 | 0.0175          | 0.065     |
| 3 | 0.203           | 0.4       |
| 4 | 0.1             | 1.29      |